

## PSMN2R8-40YSDX-VB Datasheet

### N-Channel 40-V (D-S) MOSFET

PRODUCT SUMMARY			
V <sub>DS</sub> (V)	R <sub>DS(on)</sub> (Ω)	I <sub>D</sub> (A) <sup>a, c</sup>	Q <sub>g</sub> (Typ.)
40	0.0007 at V <sub>GS</sub> = 10 V	150	80 nC
	0.0008 at V <sub>GS</sub> = 7.5 V	120	

#### FEATURES

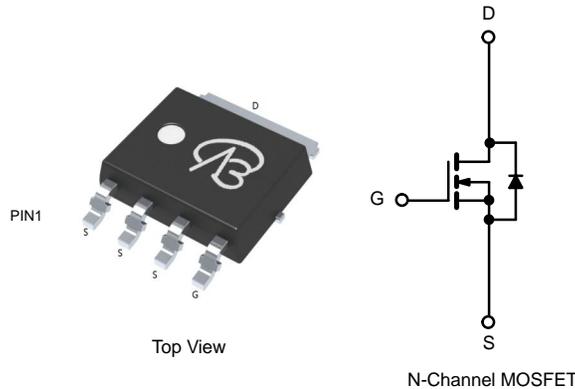
- SGT Power MOSFET
- 100 % R<sub>g</sub> and UIS Tested



**RoHS**  
COMPLIANT

#### APPLICATIONS

- Synchronous Rectification
- Power Supplies



ABSOLUTE MAXIMUM RATINGS T <sub>A</sub> = 25 °C, unless otherwise noted						
Parameter		Symbol	Limit	Unit		
Drain-Source Voltage		V <sub>DS</sub>	40	V		
Gate-Source Voltage		V <sub>GS</sub>	± 25			
Continuous Drain Current (T <sub>J</sub> = 175 °C)	T <sub>C</sub> = 25 °C	I <sub>D</sub>	150 <sup>a, c</sup>	A		
	T <sub>C</sub> = 70 °C		96 <sup>c</sup>			
	T <sub>A</sub> = 25 °C		29 <sup>b</sup>			
	T <sub>A</sub> = 70 °C		23 <sup>b</sup>			
Pulsed Drain Current		I <sub>DM</sub>	450			
Avalanche Current Pulse		L = 0.1 mH	I <sub>AS</sub>	80		
Single Pulse Avalanche Energy			E <sub>AS</sub>	320	mJ	
Continuous Source-Drain Diode Current		T <sub>C</sub> = 25 °C	I <sub>S</sub>	120 <sup>a, c</sup>	A	
				T <sub>A</sub> = 25 °C		2.6 <sup>b</sup>
Maximum Power Dissipation		T <sub>C</sub> = 25 °C	P <sub>D</sub>	375 <sup>a</sup>	W	
				T <sub>C</sub> = 70 °C		263
				T <sub>A</sub> = 25 °C		3.75 <sup>b</sup>
				T <sub>A</sub> = 70 °C		2.6 <sup>b</sup>
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	- 55 to 175	°C		

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient <sup>b</sup>	Steady State	R <sub>thJA</sub>	32	40	°C/W
Maximum Junction-to-Case	Steady State	R <sub>thJC</sub>	0.33	0.4	

Notes:

a. Based on T<sub>C</sub> = 25 °C.

b. Surface Mounted on 1" x 1" FR4 board.

c. Calculated based on maximum junction temperature. Package limitation current is 150 A.

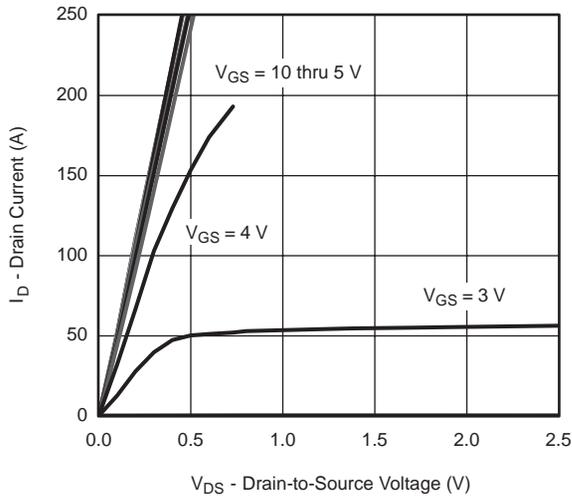
SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	40			V
$V_{DS}$ Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = 250\text{ }\mu\text{A}$		41		mV/°C
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$			- 8		
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	2		4	V
Gate-Source Leakage	$I_{GSS}$	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 40\text{ V}, V_{GS} = 0\text{ V}$			1	$\mu\text{A}$
		$V_{DS} = 40\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$			10	
On-State Drain Current <sup>a</sup>	$I_{D(on)}$	$V_{DS} \geq 5\text{ V}, V_{GS} = 10\text{ V}$	150			A
Drain-Source On-State Resistance <sup>a</sup>	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 30\text{ A}$		0.0007		$\Omega$
		$V_{GS} = 7.5\text{ V}, I_D = 20\text{ A}$		0.0008		
Forward Transconductance <sup>a</sup>	$g_{fs}$	$V_{DS} = 15\text{ V}, I_D = 30\text{ A}$		100		S
<b>Dynamic<sup>b</sup></b>						
Input Capacitance	$C_{iss}$	$V_{DS} = 20\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$		6000		pF
Output Capacitance	$C_{oss}$			1650		
Reverse Transfer Capacitance	$C_{rss}$			450		
Total Gate Charge	$Q_g$	$V_{DS} = 20\text{ V}, V_{GS} = 10\text{ V}, I_D = 20\text{ A}$		80	100	nC
Gate-Source Charge	$Q_{gs}$			30		
Gate-Drain Charge	$Q_{gd}$			16		
Gate Resistance	$R_g$	$f = 1\text{ MHz}$		0.85	1.3	$\Omega$
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 20\text{ V}, R_L = 1.0\text{ }\Omega$ $I_D \cong 20\text{ A}, V_{GEN} = 10\text{ V}, R_g = 1\text{ }\Omega$		20	30	ns
Rise Time	$t_r$			11	17	
Turn-Off Delay Time	$t_{d(off)}$			77	115	
Fall Time	$t_f$			10	15	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 20\text{ V}, R_L = 1.0\text{ }\Omega$ $I_D \cong 20\text{ A}, V_{GEN} = 4.5\text{ V}, R_g = 1\text{ }\Omega$		20		
Rise Time	$t_r$			18		
Turn-Off Delay Time	$t_{d(off)}$			50		
Fall Time	$t_f$			30		
<b>Drain-Source Body Diode Characteristics</b>						
Continuous Source-Drain Diode Current	$I_S$	$T_C = 25\text{ }^\circ\text{C}$			120	A
Pulse Diode Forward Current <sup>a</sup>	$I_{SM}$				200	
Body Diode Voltage	$V_{SD}$	$I_S = 20\text{ A}$		0.8	1.2	V
Body Diode Reverse Recovery Time	$t_{rr}$	$I_F = 20\text{ A}, di/dt = 100\text{ A}/\mu\text{s}, T_J = 25\text{ }^\circ\text{C}$		50		ns
Body Diode Reverse Recovery Charge	$Q_{rr}$			40	65	nC
Reverse Recovery Fall Time	$t_a$			20		ns
Reverse Recovery Rise Time	$t_b$			17		

Notes:

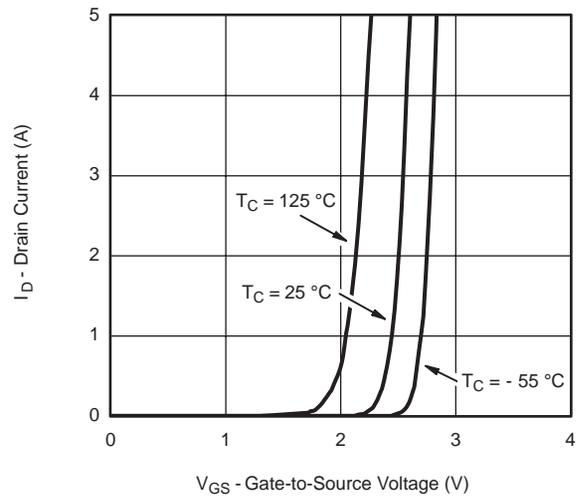
- a. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

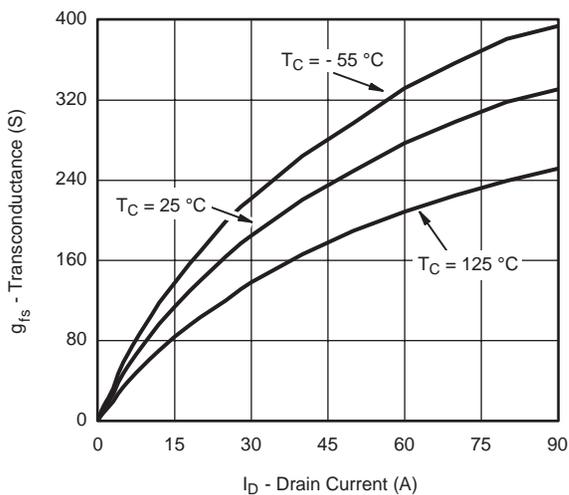
**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



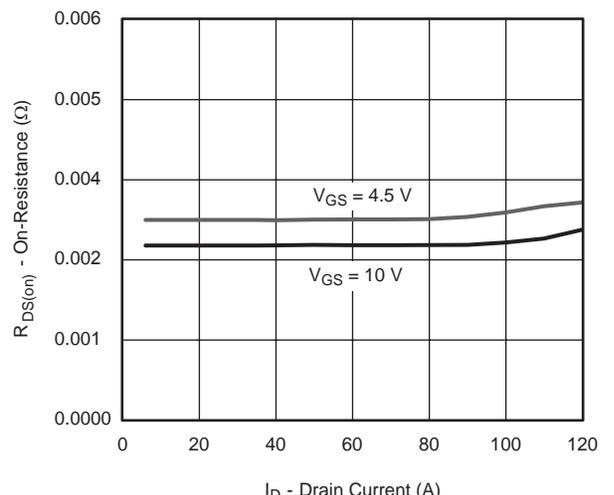
**Output Characteristics**



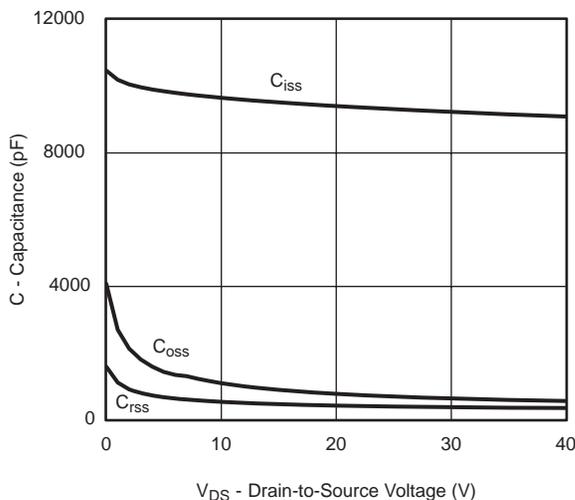
**Transfer Characteristics**



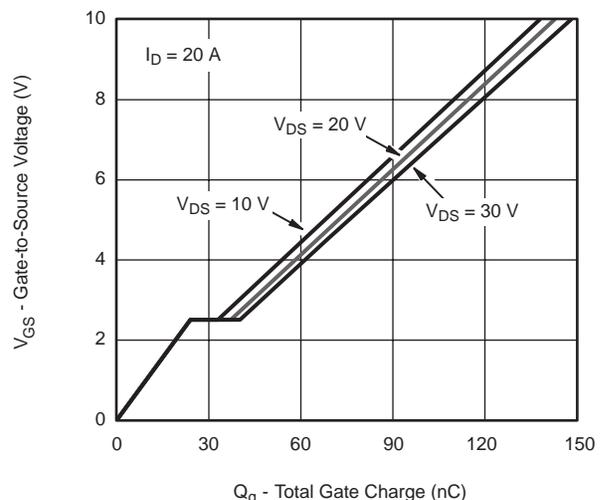
**Transconductance**



**On-Resistance vs. Drain Current**

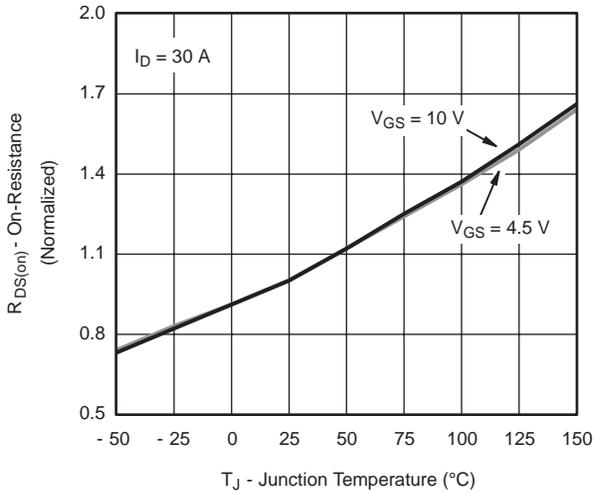


**Capacitance**

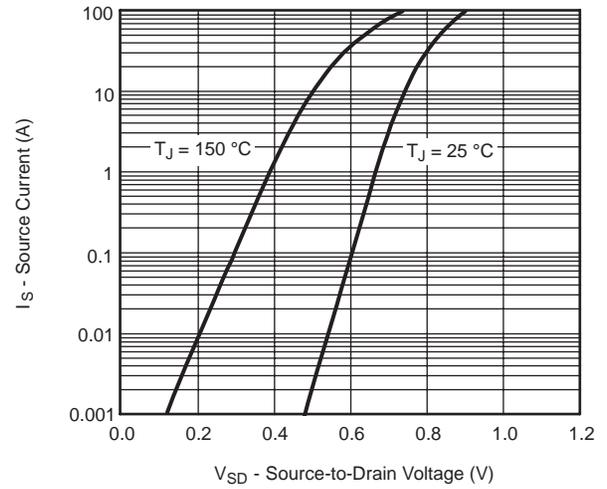


**Gate Charge**

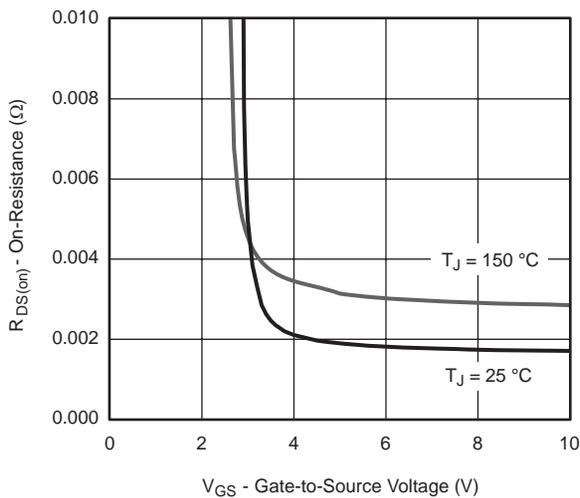
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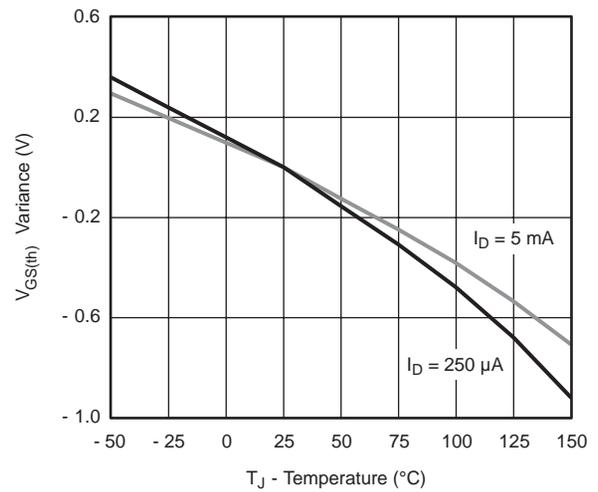
**On-Resistance vs. Junction Temperature**



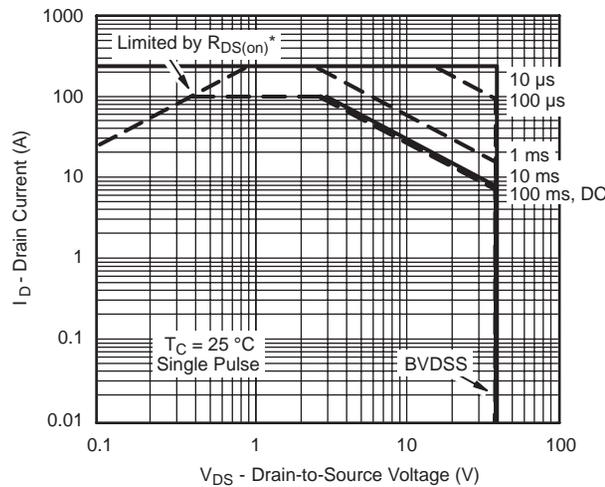
**Forward Diode Voltage vs. Temperature**



**On-Resistance vs. Gate-to-Source Voltage**



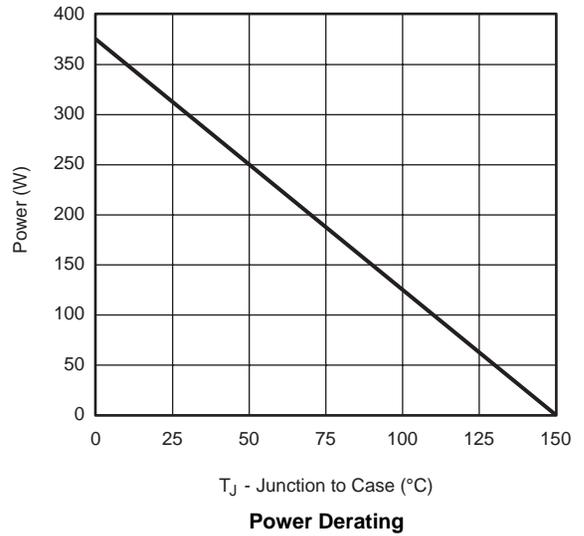
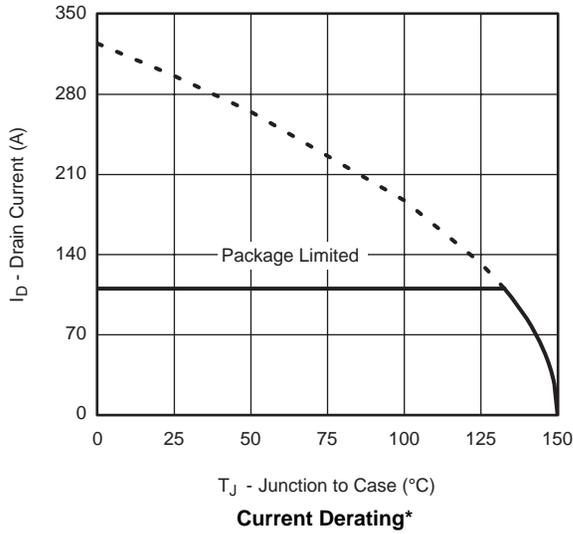
**Threshold Voltage**



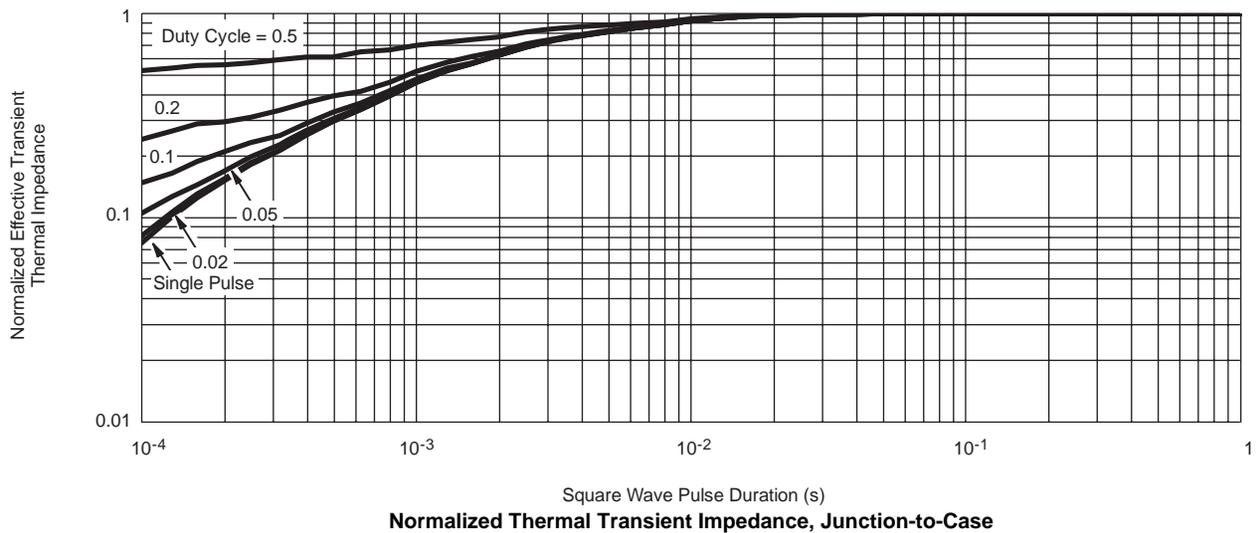
\*  $V_{GS} >$  minimum  $V_{GS}$  at which  $R_{DS(on)}$  is specified

**Safe Operating Area, Junction-to-Ambient**

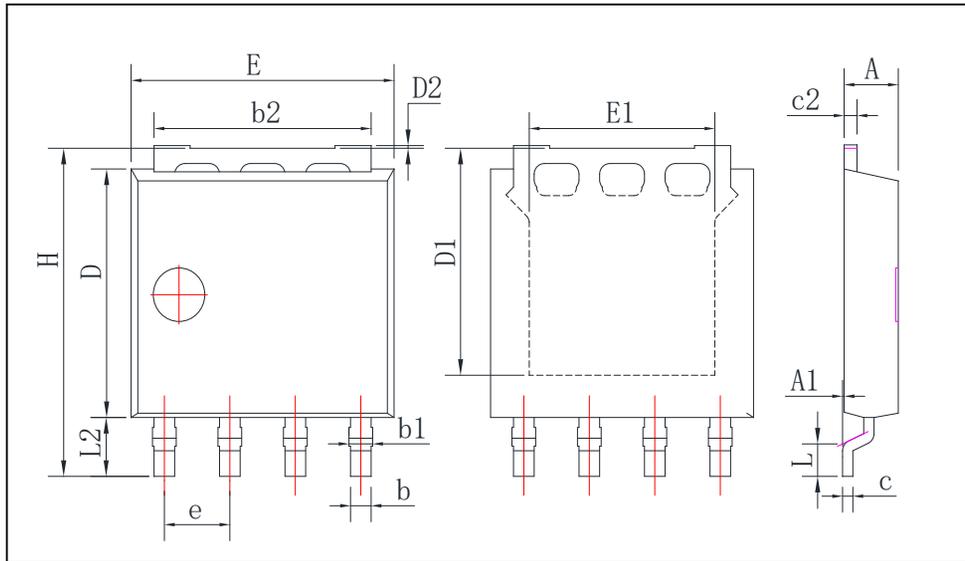
**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



\* The power dissipation  $P_D$  is based on  $T_{J(max)} = 150\text{ °C}$ , using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.



### LFPAK56 CASE OUTLINE



Symbol	Min	Typ	Max
A	1.00	1.05	1.10
A1	0.00		0.15
b	0.35	0.40	0.50
b1	0.40	0.48	0.58
b2	4.01	4.21	4.41
c	0.18	0.20	0.25
c2	0.23	0.25	0.30
D	4.44	4.59	4.70
D1	4.10	4.24	4.40
D2			0.20
e	1.22	1.27	1.32
E	5.00	5.10	5.25
E1	3.50	3.60	3.70
H	6.05	6.15	6.25
L	0.40	0.60	0.80
L2	0.90	1.10	1.30

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